

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

he the Application of

Kazuo ICHIKAWA et al.

Application No.: 09/670,877

Filed: September 27, 2000

For: CVD SUBSTRATE AND CLEANING METHOD

Group Art Unit: 1763

RECEIVEL

FEB 1 0 2003

TC 1 = -

Examiner: R. Zervigon C 170

Docket No.: 107469

#12 2411/03 MW

LARGE ENTITY REQUEST FOR CONTINUED EXAMINATION UNDER 37 C.F.R. §1.114

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. §1.114, Applicants hereby request continued examination and entry and consideration of the attached submission. The above-identified application was filed on or after June 8, 1995. Thus, entry is proper under 37 C.F.R. §1.114(d).

Attached hereto is our check no. <u>138755</u> in the amount of \boxtimes \$750.00 as payment of the fees set forth in 37 C.F.R. §1.17(e). The Director is hereby authorized to charge any additional fees or credit any overpayment associated with this communication to Deposit Account No. 15-0461. Two duplicate copies of this page are enclosed.

Respectfully submitted,

James A. Oliff

Registration No. 27,075

Stephen Tu

Registration No. 52,304

02/07/2003 CNGUYEN 00000012 09670877

02 FC:1801

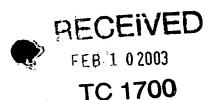
750.00 OP

JAO:SXT/amw

Date: February 6, 2003

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400 DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461





PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Kazuo ICHIKAWA et al.

Application No.: 09/670,877

Filed: September 27, 2000

CVD SUBSTRATE AND CLEANING METHOD

wpy #9

Group Art Unit: 1763

Examiner:

Docket No.:

R. Zervigon

107469

AMENDMENT

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

For:

In reply to the August 6, 2002 Office Action and in conjunction with the Request for Continued Examination filed herewith, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 3 as follows:

1. (Amended) A CVD system provided with a plasma generator having a plasma generation chamber separated from a film deposition chamber in which a substrate is arranged, wherein a material gas is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes of a lower plate, and a thin film is deposited on the substrate, said CVD system further comprising:

a cleaning gas feeder provided to said plasma generator,

said lower plate is connected to ground, and

each of said introduction holes is designed to pass the radicals only to the film deposition chamber.